

## 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications.

### 2. Features and benefits

- High blocking voltage capability
- Least sensitive gate for highest noise immunity
- High minimum I<sub>GT</sub> for guaranteed immunity to gate noise
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

### 3. Applications

- General purpose motor controls
- Lighting controls
- Applications where only positive gate drive is available
- Applications where gate noise or interference may occur

### 4. Quick reference data

| Symbol              | Parameter                                | Conditions  | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|
| V <sub>DRM</sub>    | repetitive peak off-<br>state voltage    |   | -   | -   | 600 | V    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 \text{ °C};$<br>$t_p = 20 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$     | -   | -   | 65  | A    |
| Tj                  | junction temperature                     |   | -   | -   | 125 | °C   |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; T <sub>mb</sub> ≤ 102 °C; <u>Fig. 1;</u><br><u>Fig. 2; Fig. 3</u>                           | -   | -   | 8   | A    |
| Static chara        | acteristics                              | ·   |     |     |     |      |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+};$<br>$T_j = 25 \text{ °C}; \text{ Fig. 7}$ | 10  | -   | 50  | mA   |
|                     |  | $V_D = 12 V; I_T = 0.1 A; T2+ G-;$<br>$T_j = 25 °C; Fig. 7$   | 10  | -   | 50  | mA   |





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| Symbol              | Parameter                         | Conditions   | Min | Тур | Мах | Unit |
|---------------------|-----------------------------------|--|-----|-----|-----|------|
|                     |                                   | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{7}$ | 10  | -   | 50  | mA   |
|                     |                                   | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>              | 10  | -   | 100 | mA   |
| Dynamic chara       | acteristics                       |  |     | ·   |     |      |
| dV <sub>D</sub> /dt | rate of rise of off-state voltage | $V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit   | 200 | -   | -   | V/µs |

# 5. Pinning information

| Table 2. | Pinning | information                       |                    |                |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin      | Symbol  | Description                       | Simplified outline | Graphic symbol |
| 1        | T1      | main terminal 1                   | mb                 | T2             |
| 2        | Т2      | main terminal 2                   |                    | Sym051         |
| 3        | G       | gate                              |                    | ·              |
| mb       | Τ2      | mounting base; main<br>terminal 2 |                    |                |
|          |         |                                   | TO-220AB (SOT78)   |                |

# 6. Ordering information

| Table 3. Ordering | g information |  |         |
|-------------------|---------------|--|---------|
| Type number       | Package       |  |         |
|                   | Name          | Description  | Version |
| BT137-600-0       | TO-220AB      | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

## 7. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
| BT137-600-0            | BT137-600 0  |

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# 8. Limiting values

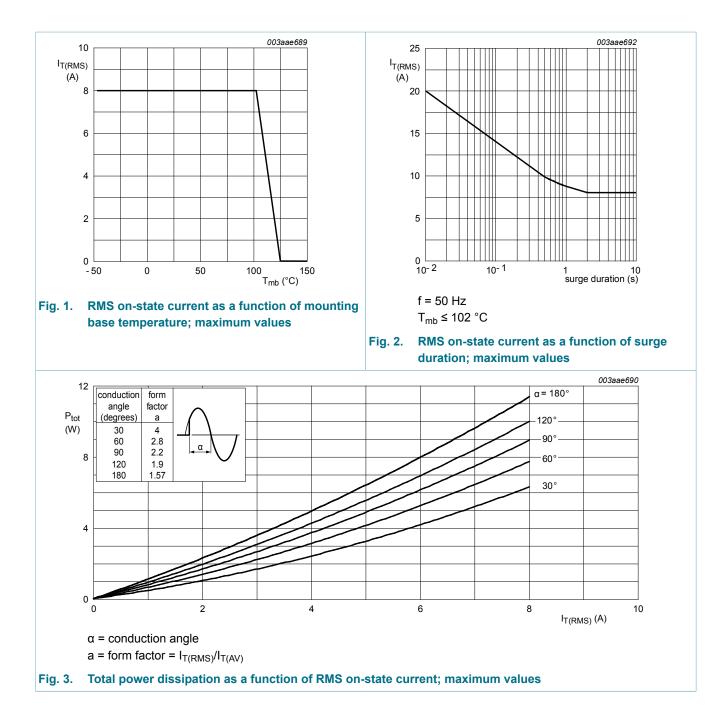
#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions  | Min | Max | Unit             |
|---------------------|--------------------------------------|---|-----|-----|------------------|
| V <sub>DRM</sub>    | repetitive peak off-state voltage    |   | -   | 600 | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; $T_{mb} \le 102 \text{ °C}$ ; Fig. 1;<br>Fig. 2; Fig. 3                 | -   | 8   | A                |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C};$<br>$t_p = 20 \text{ ms}; Fig. 4; Fig. 5$ | -   | 65  | A                |
|                     |                                      | full sine wave; $T_{j(init)}$ = 25 °C;<br>$t_p$ = 16.7 ms                               | -   | 71  | A                |
| l <sup>2</sup> t    | I <sup>2</sup> t for fusing          | t <sub>p</sub> = 10 ms; sine-wave pulse   | -   | 21  | A <sup>2</sup> s |
| dl <sub>T</sub> /dt | rate of rise of on-state current     | $I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs;<br>T2+ G+                            | -   | 50  | A/µs             |
|                     |                                      | $I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs;<br>T2+ G-                            | -   | 50  | A/µs             |
|                     |                                      | $I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs;<br>T2- G-                            | -   | 50  | A/µs             |
|                     |                                      | $I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs;<br>T2- G+                            | -   | 10  | A/µs             |
| I <sub>GM</sub>     | peak gate current                    |   | -   | 2   | А                |
| P <sub>GM</sub>     | peak gate power                      |   | -   | 5   | W                |
| P <sub>G(AV)</sub>  | average gate power                   | over any 20 ms period   | -   | 0.5 | W                |
| T <sub>stg</sub>    | storage temperature                  |   | -40 | 150 | °C               |
| Tj                  | junction temperature                 |   | -   | 125 | °C               |

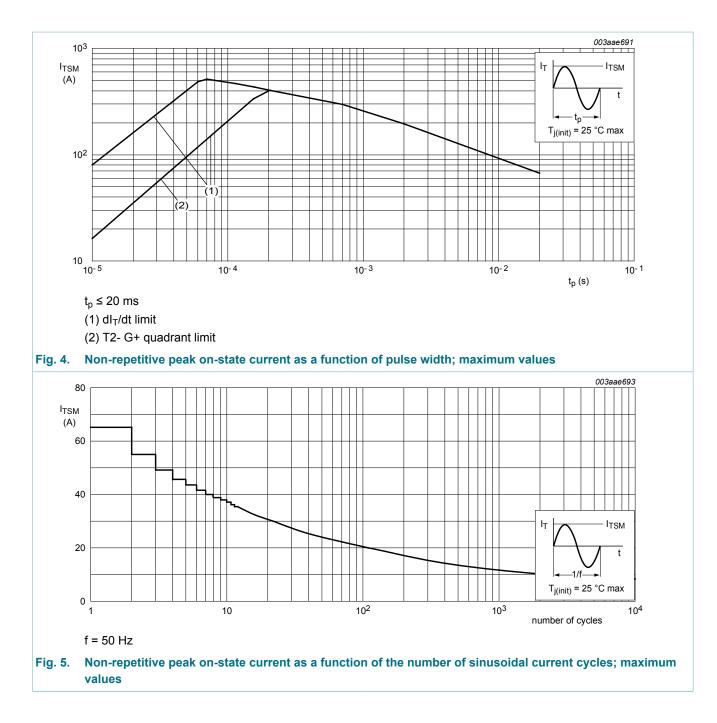
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# BT137-600-0

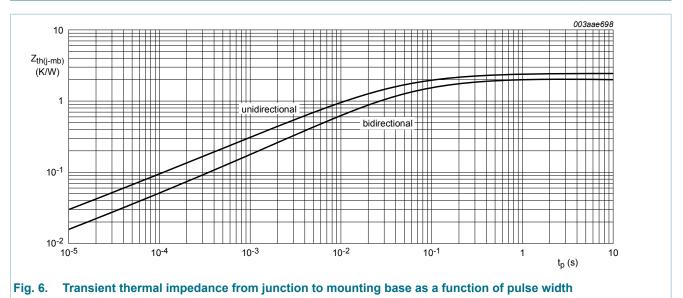
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## 9. Thermal characteristics

| Table 6. The         | ermal characteristics                             |                           |     |     |     |      |
|----------------------|---|---------------------------|-----|-----|-----|------|
| Symbol               | Parameter   | Conditions                | Min | Тур | Max | Unit |
| from junct           | thermal resistance                                | full cycle; <u>Fig. 6</u> | -   | -   | 2   | K/W  |
|                      | from junction to<br>mounting base                 | half cycle; Fig. 6        | -   | -   | 2.4 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance<br>from junction to<br>ambient | in free air               | -   | 60  | -   | K/W  |



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# **10. Characteristics**

| Symbol                | Parameter                             | Conditions   | Min  | Тур | Max  | Unit |
|-----------------------|---------------------------------------|--|------|-----|------|------|
| Static chara          | cteristics                            |  |      |     |      |      |
| Gт                    | gate trigger current                  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                                  | 10   | -   | 50   | mA   |
|                       |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                                  | 10   | -   | 50   | mA   |
|                       |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                                  | 10   | -   | 50   | mA   |
|                       |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 7</u>                                  | 10   | -   | 100  | mA   |
| L                     | latching current                      | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 8</u>                                  | -    | -   | 45   | mA   |
|                       |                                       | $V_D$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-;<br>T <sub>j</sub> = 25 °C; <u>Fig. 8</u>   | -    | -   | 60   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$<br>T <sub>j</sub> = 25 °C; Fig. 8                             | -    | -   | 45   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$<br>T <sub>j</sub> = 25 °C; Fig. 8                             | -    | -   | 60   | mA   |
| Ін                    | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>   | -    | -   | 40   | mA   |
| V <sub>T</sub>        | on-state voltage                      | I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>  | -    | 1.3 | 1.65 | V    |
| V <sub>GT</sub>       | gate trigger voltage                  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C;<br>Fig. 11  | -    | 0.7 | 1    | V    |
|                       |                                       | V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C;<br>Fig. 11  | 0.25 | 0.4 | -    | V    |
| D                     | off-state current                     | V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C  | -    | 0.1 | 0.5  | mA   |
| Dynamic ch            | aracteristics                         | II   |      |     |      |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 402 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit | 200  | -   | -    | V/µs |
| dV <sub>com</sub> /dt | rate of change of commutating voltage | $V_D$ = 400 V; T <sub>j</sub> = 95 °C; dI <sub>com</sub> /dt = 3.6 A/<br>ms; I <sub>T</sub> = 8 A; gate open circuit             | 10   | -   | -    | V/µs |
| lgt                   | gate-controlled turn-on time          | I <sub>TM</sub> = 12 A; V <sub>D</sub> = 600 V; I <sub>G</sub> = 0.1 A; dI <sub>G</sub> /<br>dt = 5 A/μs                         | -    | 2   | -    | μs   |

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140

Tj (°C)

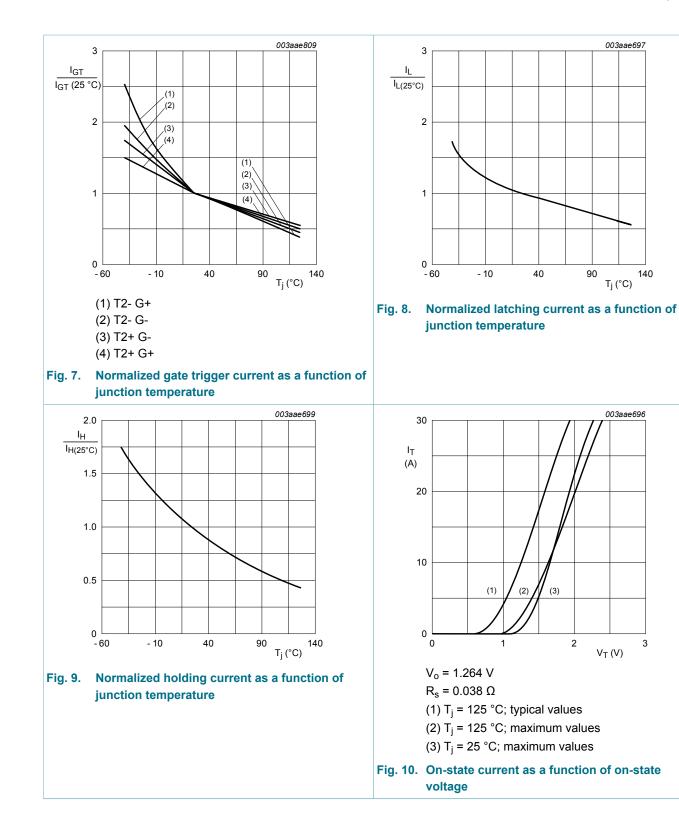
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3

V<sub>T</sub> (V)

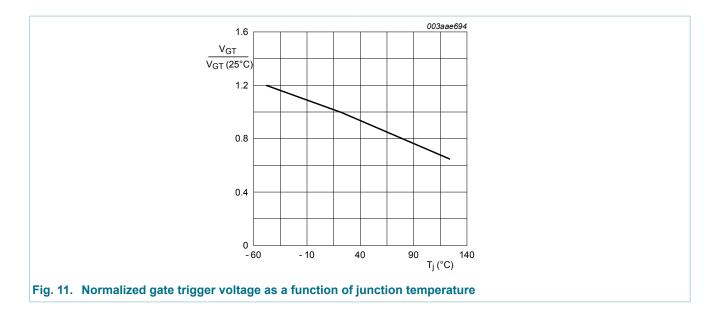
003aae697

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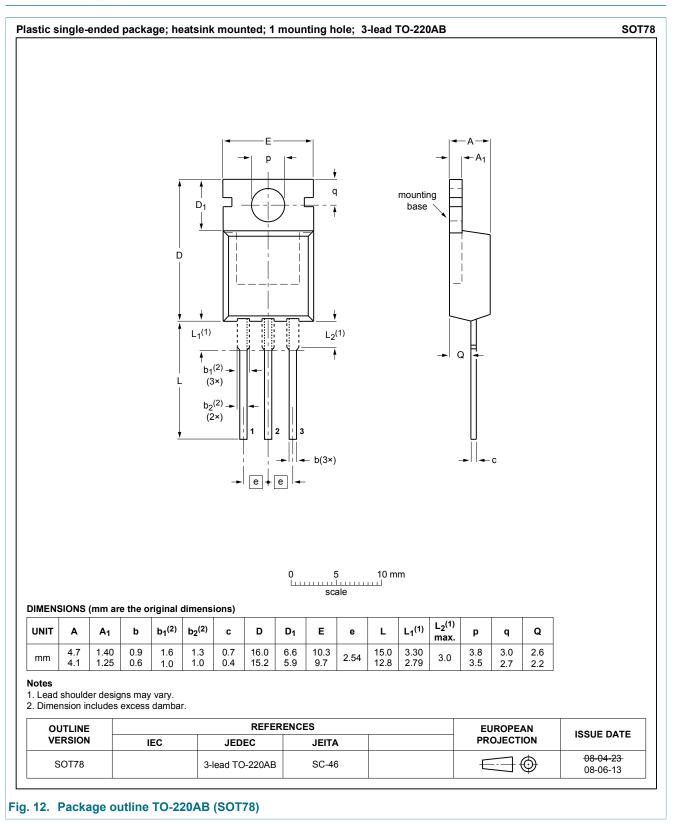


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### 11. Package outline



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|--------------------------------------|-------------------------------|---|
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